

*“InAs p-n diodes grown on GaAs and GaAs-coated Si by molecular beam epitaxy”.*  
Dobbelaere W, de Boeck J, Heremans P, Mertens R, Borghs G, Luyten W, van Landuyt J,  
Applied physics letters **60**, 868 (1992). <http://doi.org/10.1063/1.106490>